# **IGBT Ignition Predriver with Dynamic Current Regulation**

The CS8312 is a bipolar microprocessor interface IC designed to drive an IGBT (or logic level MOSFETs) powering large inductive loads in harsh operating environments. The IC's dynamic current limit function lets the microprocessor adjust the current limit threshold to the real time needs of the system.

CLI, the current limit input, sets the current limit for the IGBT high or low as directed by the system microprocessor. CLI also raises and lowers the threshold on the diagnostic FLAG output signal. The FLAG output signals the microprocessor when the current level approaches current limit on the IGBT. The CTRL input enables the FLAG function.

#### **Features**

- µP Compatible Inputs
- Adjustable Current Limit Thresholds
- External Sense Resistor
- Flag Signal to Indicate Output Status

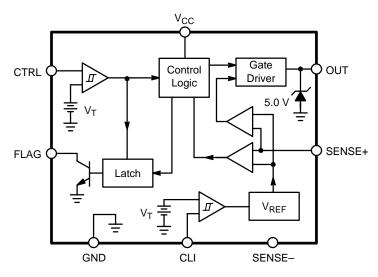


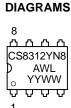
Figure 1. Block Diagram



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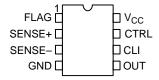
**MARKING** 





A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week

#### **PIN CONNECTIONS**



#### **ORDERING INFORMATION**

Device	Device Package	
CS8312YN8	DIP-8	50 Units/Rail
CS8312YD8	SO-8	95 Units/Rail
CS8312YDR8	SO-8	2500 Tape & Reel

#### **ABSOLUTE MAXIMUM RATINGS\***

Rati	Value	Unit	
Supply Voltage	Supply Voltage		
Digital Input Currents	2.0	mA	
Internal Power Dissipation (T <sub>A</sub> = 25°C)		700	mW
Junction Temperature Range	-40 to +150	°C	
Storage Temperature Range	-55 to +165	°C	
Electrostatic Discharge (Human Body Model)		2.0	kV
Lead Temperature Soldering	Wave Solder (through hole styles only) Note 1. Reflow (SMD styles only) Note 2.	260 peak 230 peak	°C °C

<sup>1. 10</sup> seconds max.

#### $\textbf{ELECTRICAL CHARACTERISTICS} \quad (7.0 \text{ V} \leq \text{V}_{CC} \leq 10 \text{ V}, -40^{\circ}\text{C} \leq \text{T}_{A} \leq 125^{\circ}\text{C},$

 $-0.2~V \le Differential~Ground~Voltage \le 0.8~V;$  unless otherwise specified.)

Characteristic	Test Conditions	Min	Тур	Max	Unit
General					
Power Supply Including Ripple Voltage	-	7.0	-	10	V
Supply Ripple Frequency	-	10	-	60	kHz
Differential Ground Frequency	-	10	-	60	kHz
Quiescent Current, I <sub>Q</sub> Turn On Turn Off	V <sub>CTRL</sub> = 5.5 V V <sub>CTRL</sub> = -0.3 V	- -	_ _	15 5.0	mA mA
Supply Voltage Rejection	V <sub>CTRL</sub> = 5.5 V	30	-	-	dB
Differential Ground Rejection Ratio	V <sub>CTRL</sub> = 5.5 V	30	-	-	dB
Differential Ground Current Ratio	$V_{CTRL} = -0.3 \text{ V},$ $(V_{SENSE-} - V_{GND})DC = 1.0 \text{ V}$ $(V_{SENSE-} - V_{GND})AC = 0.6 \text{ V}$	-	_	3.0	mA
Unity Gain Bandwidth	V <sub>CTRL</sub> = 5.5 V	400	_	_	kHz
Turn On Delay	CTRL Increasing	_	-	30	μs
Turn Off Delay	CTRL Decreasing	-	-	30	μs
Control Function					
Input Voltage Range	I <sub>CTRL</sub> = 2.0 mA	-0.3	-	5.5	V
Input Threshold Turn On Turn Off Hysteresis	CTRL Increasing CTRL Decreasing	- 1.5 0.4	- - -	3.5 - 2.0	V V
Voltage	I <sub>CTRL</sub> = 10 μA max	-	_	1.1	V
Input Capacitance	-	_	-	50	pF
Current Limit Increase Function		•	•	•	•
Input Voltage Range	I <sub>CTRL</sub> = 2.0 mA	-0.3	-	5.5	V
Input Threshold Turn On Turn Off Hysteresis	CLI Increasing CLI Decreasing	- 1.5 0.4	- - -	3.5 - 2.0	V V V
Voltage I <sub>CLI</sub> = 10 μA max		_	_	1.1	V

<sup>2. 60</sup> seconds max above 183°C

<sup>\*</sup>The maximum package power dissipation must be observed.

### **ELECTRICAL CHARACTERISTICS (continued)** (7.0 V $\leq$ V<sub>CC</sub> $\leq$ 10 V, $-40^{\circ}$ C $\leq$ T<sub>A</sub> $\leq$ 125 $^{\circ}$ C,

 $-0.2~V \le Differential~Ground~Voltage \le 0.8~V;~unless~otherwise~specified.)$ 

Characteristic	Test Conditions	Min	Тур	Max	Unit			
Current Limit Increase Function (continued)								
Input Capacitance	-	-	-	50	pF			
Output Stage								
Гоит	-	-	-	5.0	mA			
Clamp Voltage	V <sub>CTRL</sub> = 5.5 V, I <sub>OUT</sub> = 1.0 mA	4.0	-	5.5	V			
Output Off Voltage	$V_{CTRL} = -0.3 \text{ V, } I_{OUT} = 10 \mu\text{A}$ $V_{CTRL} = -0.3 \text{ V, } I_{OUT} = 200 \mu\text{A}$		_ _	0.5 1.2	V			
Flag Function								
Output Low	V <sub>CTRL</sub> = 5.5 V, I <sub>FLAG</sub> = 1.5 mA	-	-	0.9	V			
Leakage Current	V <sub>CTRL</sub> = -0.3 V	-	-	10	μΑ			
Output Capacitance	-	-	-	50	pF			
Turn On (V <sub>SENSE+</sub> – V <sub>SENSE</sub> -)	V <sub>CTRL</sub> = 5.5 V, V <sub>CLI</sub> = -0.3 V V <sub>CTRL</sub> = 5.5 V, V <sub>CLI</sub> = 5.5 V	210 300	225 -	240 350	mV mV			
Turn Off Delay	CTRL Decreasing	-	-	10	μs			
Turn On Delay	-	_	-	10	μs			
Disable Time	-	100	-	450	μs			
Sense Function								
Input Voltage Range	-		-	2.5	V			
Sense Regulation Voltage	V <sub>CTRL</sub> = 5.5 V, V <sub>CLI</sub> = -0.3 V V <sub>CTRL</sub> = 5.5 V, V <sub>CLI</sub> = 5.5 V	270 380	295 410	320 440	mV mV			
Input Leakage Current	V <sub>CTRL</sub> = 5.5 V	-	-	5.0	μΑ			
Propagation Delay	V <sub>CTRL</sub> = 5.5 V	_	-	20	μs			

#### PACKAGE PIN DESCRIPTION

PACKA	GE PIN #		
DIP-8	SO-8	PIN SYMBOL	FUNCTION
1	1	FLAG	Indicates whether current through the IGBT has reached a preset level.
2	2	SENSE+	Positive input to current comparator.
3	3	SENSE-	Ground (SENSE-) for current sense resistor.
4	4	GND	Ground connection.
5	5	OUT	Output voltage to IGBT (MOSFET) gate.
6	6	CLI	Current limit input increase.
7	7	CTRL	Control input.
8	8	V <sub>CC</sub>	Supply voltage.

#### **CIRCUIT DESCRIPTION**

#### Flag Function (See Figure 2)

The flag indicates when the voltage across the two sense pins is approaching a current limit level that has been determined by the value of the external sense resistor (R<sub>SENSE</sub>) and the state of the CTRL and CLI pins. If the voltage across the sense pins (SENSE+, SENSE-) is less than the flag turn-on voltage, then the FLAG is off. When the voltage between the sense pins equals the FLAG turn on voltage, the FLAG will latch on until the CTRL pin goes low. FLAG is disabled whenever CTRL is low. Changing the CLI pin from low to high will increase nominal FLAG turn on voltage by approximately 45%.

**Table 1. FLAG Timing Sequence** 

State	CONTROL	CONTROL SENSE+	
0	Low	X	OFF
1	High	Below Threshold	OFF
2	High	Above Threshold	ON
3	High	X	ON
0	Low	X	OFF

#### **Output Stage**

The CS8312 output (OUT) saturates and supplies voltage to the IGBT (or MOSFET) gate once the CTRL switches from low to high. As current through the IGBT (MOSFET) increases and the voltage across the sense resistor passes the flag turn on voltage, the FLAG will turn on. If the current through the sense resistor continues to rise and the sense resistor voltage reaches the regulation sense voltage, then the gate voltage will fall to a level that regulates the driver and maintains the regulation sense voltage at the sense resistor.

#### **Current Limit Function**

Changing the CLI pin from a logic low to a logic high increases the FLAG turn on voltage by approximately 45% and the regulation sense voltage by approximately 39% respectively.

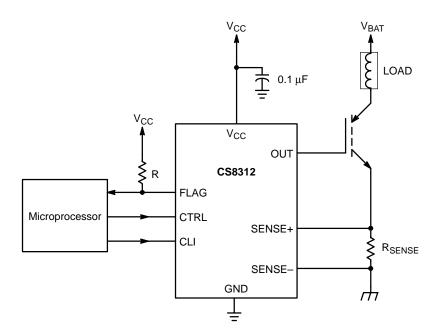
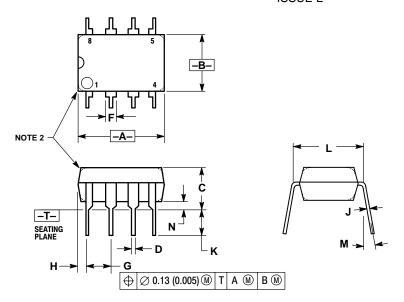


Figure 2. Application and Test Diagram

#### **PACKAGE DIMENSIONS**

#### DIP-8 **N SUFFIX** CASE 626-05 **ISSUE L**



- IOTES:

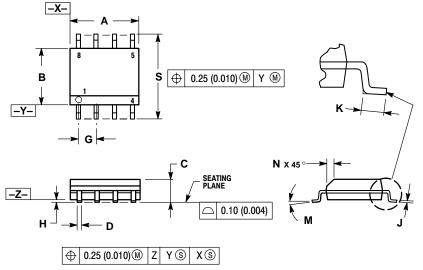
  1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

  2. PACKAGE CONTOUR OPTIONAL (ROUND OR SOUARE CORNERS).

  3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.40	10.16	0.370	0.400
В	6.10	6.60	0.240	0.260
С	3.94	4.45	0.155	0.175
D	0.38 0.51		0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54	BSC	0.100 BSC	
Н	0.76	1.27	0.030	0.050
_	0.20	0.30	0.008	0.012
K	2.92	3.43	0.115	0.135
L	7.62 BSC		0.300	BSC
M		10°		10°
N	0.76	1.01	0.030	0.040

#### SO-8 **D SUFFIX** CASE 751-07 ISSUE W



#### NOTES:

- NOTES:
  1 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER CIDE.
- SIDE.
  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN
  EXCESS OF THE D DIMENSION AT MAXIMUM
  MATERIAL CONDITION.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	7 BSC	0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

#### **PACKAGE THERMAL DATA**

Parameter		DIP-8	SO-8	Unit
$R_{\Theta JC}$	Typical	52	45	°C/W
$R_{\Theta JA}$	Typical	100	165	°C/W

## **Notes**

## **Notes**

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